

● General Description

Through advanced trench and field cutoff technology to provide very low $V_{CE(sat)}$, low gate charge, and excellent switching performance.

● Features

- Very low $V_{CE(sat)}$
- Low switching power loss
- Low switching surge and noise
- Low thermal resistance

● Application

- Energy Generation
- Industrial power supplies
- Welding

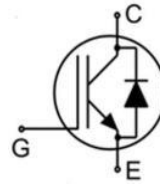
● Ordering Information:

Part NO.	ZMBG030N065DAB
Marking	BG030N065DA
Packing information	REEL TAPE
Basic ordering unit (pcs)	800

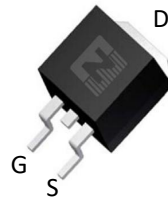
● Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Collector-emitter voltage	V_{CE}		650	V
Gate-emitter voltage	V_{GE}		± 20	V
Collector current	I_C	$T_C=25^\circ\text{C}$	60	A
	I_C	$T_C=100^\circ\text{C}$	30	A
Pulsed collector current	I_{CM}		90	A
Diode forward current	I_F	$T_C=25^\circ\text{C}$	30	A
	I_F	$T_C=100^\circ\text{C}$	15	A
	$I_{F,pulse}$		60	A
Total power Dissipation	P_D	$T_C=25^\circ\text{C}$	250	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.8	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +150	$^\circ\text{C}$

● Product Summary



$V_{CE} = 650\text{V}$
 $V_{CE(sat)} = 1.55\text{V}$
 $I_C = 30\text{A}$



TO-263



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case IGBT	R_{thJC}		-	0.6	°C/W
Thermal resistance, junction - case diode	R_{thJC}		-	1.4	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{\textcircled{2}}$		-	40	°C/W
Soldering temperature (total time<10s)	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 250\mu A$	650			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C = 30A$		1.53	1.8	V
		$V_{GE} = 15V, I_C = 30A, T_J = 125^\circ C$		1.63		
		$V_{GE} = 15V, I_C = 30A, T_J = 175^\circ C$		1.73		
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 1mA$	4.0	5.0	6.0	V
Forward on-voltage	V_F	$I_F = 15A, T_J = 25^\circ C$		1.2	1.5	V
		$I_F = 15A, T_J = 125^\circ C$		1.1	1.4	
		$I_F = 15A, T_J = 175^\circ C$		1.0	1.3	
Zero gate voltage collector current	I_{CES}	$V_{GE} = 0V, V_{CE} = 650V$			50.0	uA
Gate-emitter leakage current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0V$			100	nA

•Dynamic characteristics , at $T_J = 25^\circ C$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{ies}	$f = 1MHz, V_{CE} = 25V$	-	2440	-	pF
Output capacitance	C_{oes}		-	163	-	
Reverse transfer capacitance	C_{res}		-	30	-	
Total gate charge	Q_g	$V_{CC} = 520V, I_C = 20.0A, V_{GE} = 15V$	-	82	-	nC
Gate-emitter charge	Q_{ge}		-	18	-	nC
Gate-collector charge	Q_{gc}		-	31	-	nC

Switching Characteristic, at $T_J=25^\circ\text{C}$

Turn-on delay time	$t_{D(on)}$	$T_J=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=30.0\text{A}$, $V_{GE}=-15.0/15.0\text{V}$, $R_g=10.0\Omega$, $L=105\mu\text{H}$	-	20	-	ns
Turn-on rise time	t_r		-	20	-	ns
Turn-off delay time	$t_{D(off)}$		-	70	-	ns
Turn-off fall time	t_f		-	65	-	ns
Turn-on energy	E_{on}			945		μJ
Turn-off energy	E_{off}			484		μJ
Total switching energy	E_{ts}			1429		μJ

Switching Characteristic, at $T_J=150^\circ\text{C}$

Turn-on delay time	$t_{D(on)}$	$T_J=150^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=30.0\text{A}$, $V_{GE}=-15.0/15.0\text{V}$, $R_g=10.0\Omega$, $L=105\mu\text{H}$	-	19	-	ns
Turn-on rise time	t_r		-	18	-	ns
Turn-off delay time	$t_{D(off)}$		-	81	-	ns
Turn-off fall time	t_f		-	90	-	ns
Turn-on energy	E_{on}			1030		μJ
Turn-off energy	E_{off}			627		μJ
Total switching energy	E_{ts}			1657		μJ

Diode switching characteristics (inductive load)

Reverse recovery time	t_{rr}	$I_F=20\text{A}$, $V_R=400\text{V}$, $di/dt = 1000\text{ A}/\mu\text{s}$ $T_J=25^\circ\text{C}$	-	28	-	ns
Reverse recovery charge	Q_{rr}		-	189	-	nC
Reverse recovery current	I_{rrm}		-	11.8	-	A
Reverse recovery energy	E_{rr}		-	78	-	μJ
Reverse recovery time	t_{rr}	$I_F=20\text{A}$, $V_R=400\text{V}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $T_J=175^\circ\text{C}$	-	139	-	ns
Reverse recovery charge	Q_{rr}		-	1160	-	nC
Reverse recovery current	I_{rrm}		-	16.8	-	A
Reverse recovery energy	E_{rr}		-	167	-	μJ

Fig.1 Gate-Charge characteristics

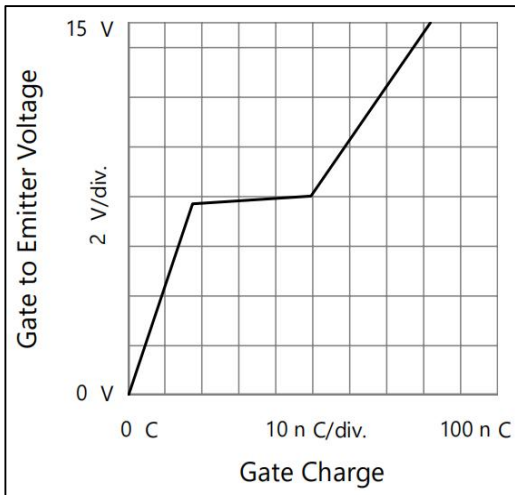


Fig.2 Capacitance characteristics

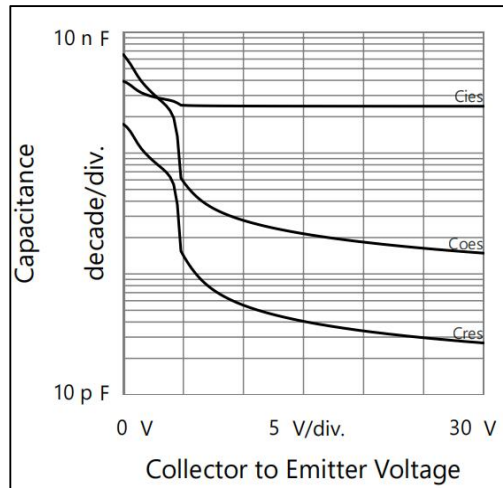


Fig.3 Power dissipation

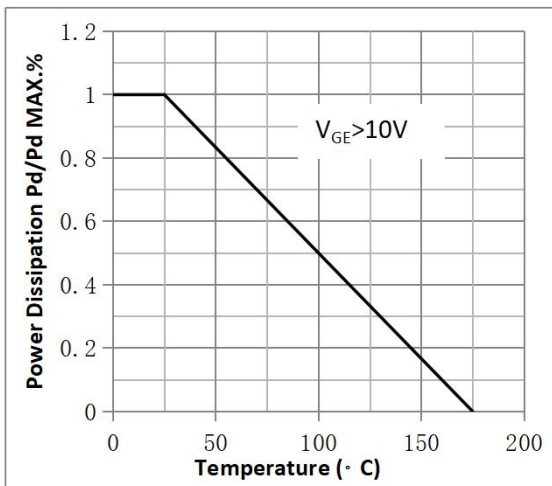


Fig.4 Typical output characteristics

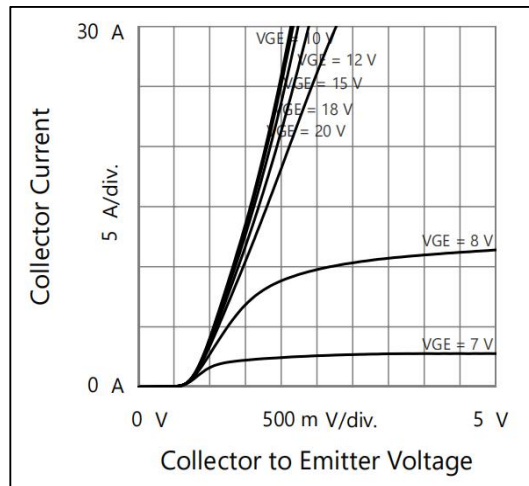


Fig.5 Threshold voltage V.S junction temperature

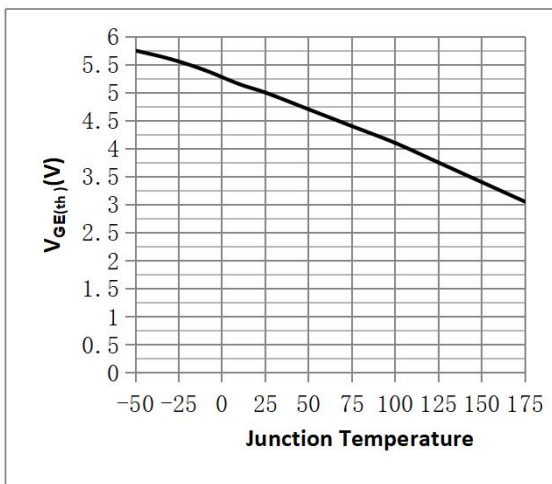


Fig.6 IC vs. Junction Temperature^③

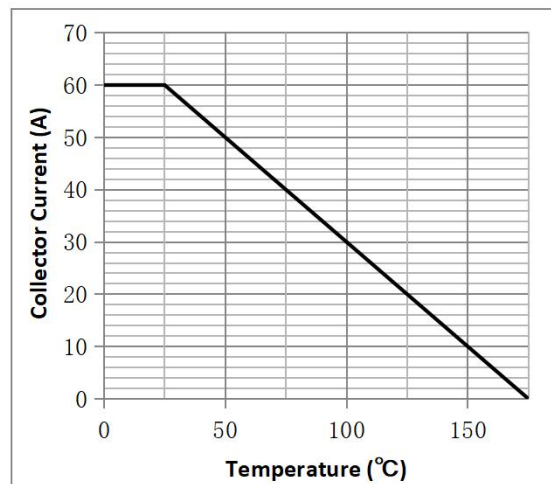


Fig.7 Collector-Emitter VS gate source voltage

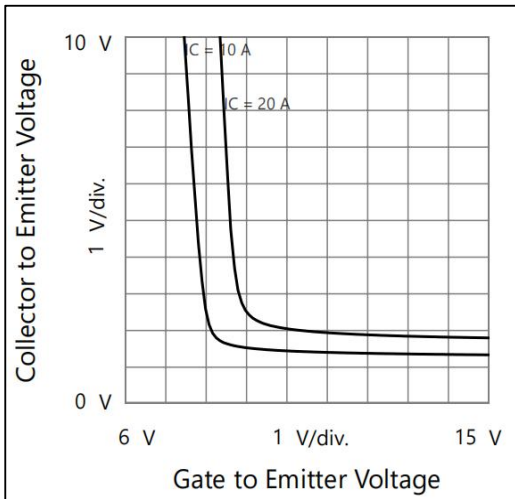


Figure 8. Transfer characteristics

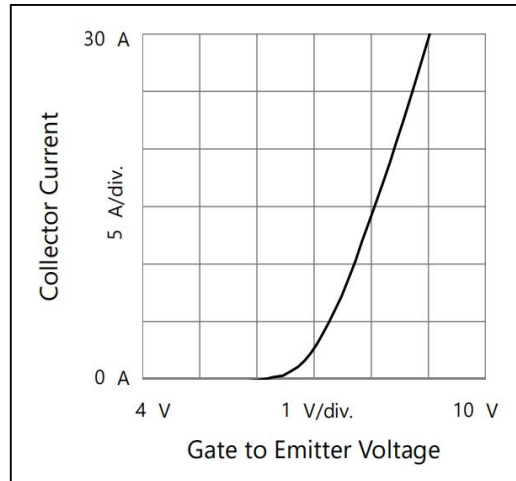


Fig.9 Safe operating area

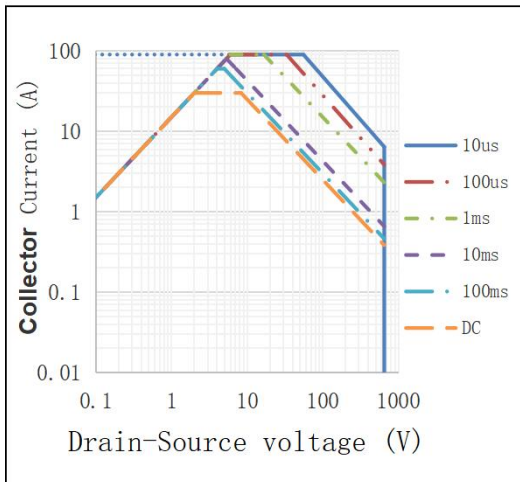


Fig.10 Max transient thermal impedance for IGBT

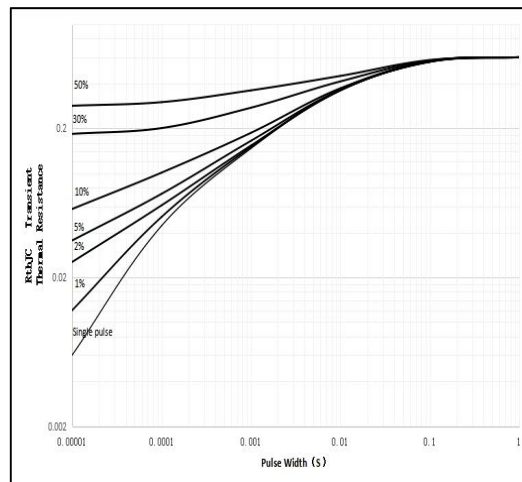
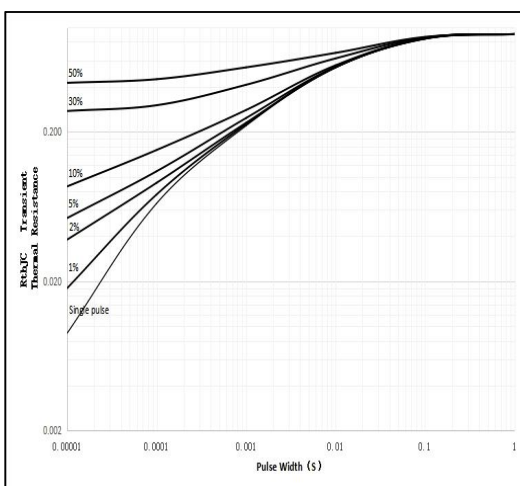
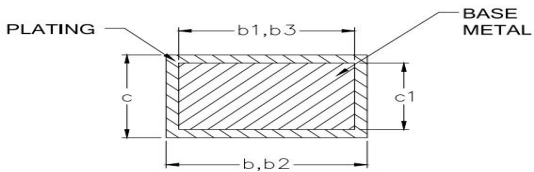
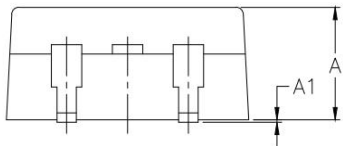
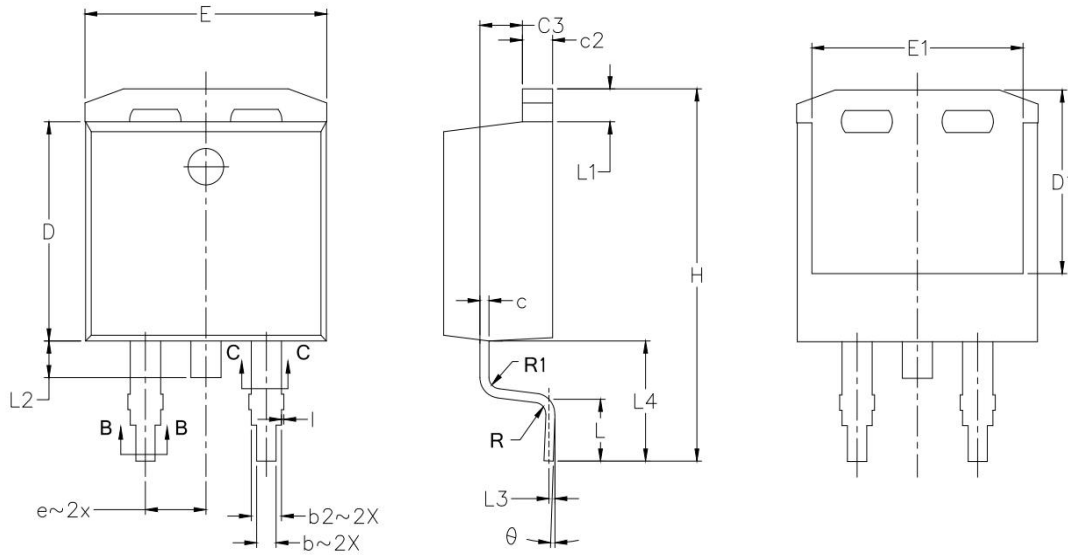


Fig.11 Max transient thermal impedance for Diode



TO-263 Package Outline



SYMBOLS	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	4.064	4.826	0.160	0.190
A1	0.000	0.254	0.000	0.010
b	0.508	0.991	0.020	0.039
b1	0.508	0.889	0.020	0.035
b2	1.143	1.778	0.045	0.070
b3	1.143	1.727	0.045	0.068
c	0.381	0.737	0.015	0.029
c1	0.381	0.584	0.015	0.023
c2	1.143	1.651	0.045	0.065
D	8.382	9.652	0.330	0.380
D1	6.858	—	0.270	—
E	9.652	10.668	0.380	0.420
E1	6.223	—	0.245	—
e	2.540 BSC.		0.100 BSC.	
H	14.605	15.875	0.575	0.625
L	1.778	2.794	0.070	0.110
L1	—	1.676	—	0.066
L2	—	1.778	—	0.070
L3	0.254 BSC		0.010 BSC	
L4	4.780	5.280	0.188	0.208
R	0.460 TYP		0.018 TYP	
R1	0.460 TYP		0.018 TYP	
theta	0°	8°	0°	8°
C3	1.68	1.88	0.0661	0.0740
I	—	0.100	—	0.0039

Note:

① Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$, Accumulation time ≤ 50 hours; For DC , the following test conditions can be passed: VGE=20V/-10V, Tj=175°C, t=1000 hours;

② Practically the current will be limited by PCB, thermal design and operating temperature. VGE=15V.

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Revision History

Version	Date	Change
A	2024.4.6	New
B	2024.7.23	Correct Eon Unit